

CLAIM SET AS AMENDED

1-4. (Canceled)

5. (Currently Amended) A method for manufacturing a semiconductor device comprising:

preparing a semiconductor substrate of a first conductivity type;

~~forming scribe lanes of the first conductivity type in the semiconductor substrate, said scribe lanes defining chip formation areas and containing only an unetched portion of the semiconductor substrate;~~

defining the semiconductor substrate with chip formation areas and scribe lane areas which define and isolate each chip formation area;

forming a mask on the semiconductor substrate to open all chip formation areas except the scribe lane areas;

forming a deep well area in each chip formation area by implanting an impurity of a second conductivity type using the mask and forming the scribe lane areas, each deep well area having a second conductivity type opposite the first conductivity type and the scribe lane areas having the first conductivity type;

removing the mask; and

forming at least one well area within the deep well area.

6. (Currently Amended) The method of claim 5, ~~further comprising forming a~~ wherein the mask is formed on the semiconductor substrate such that the deep well areas are formed in the chip formation areas and not in the scribe lanes.

7. (Previously Presented) The method of claim 5, wherein, the first conductivity type is a p-type conductor; and the second conductivity type is a n-type conductor.

8-9. (Canceled)

10. (Currently Amended) A method for manufacturing a semiconductor device comprising:

preparing a semiconductor substrate of a first conductivity type;

forming scribe lanes of the first conductivity type in the semiconductor substrate, said scribe lanes ~~defining~~ isolating chip formation areas and containing only an unetched portion of the semiconductor surface;

forming a deep well area in all areas of each chip formation area except the scribe lanes, each deep well area having a second conductivity type opposite the first conductivity type; and

~~wherein~~ forming separately a first conductive well area and a second conductive well area ~~are separately formed~~ within the deep well area,

wherein the first conductive well area is formed of the first conductivity type, and

the second conductive well area is formed of the second conductivity type.

11. (Previously Presented) The method of claim 5, wherein the scribe lanes are formed at all portions surrounding the chip formation areas.

12. (Currently Amended) The method of claim 6 5, ~~further comprising removing wherein~~ the mask is removed using plasma processing or plasma equipment.

13. (New) The method of claim 5, wherein each chip formation area is separated from each other by the scribe lane areas and is surrounded by the scribe lane areas.

14. (New) The method of claim 5, wherein the deep well area is formed in all areas of each chip formation area.

15. (New) The method of claim 5, wherein the first conductivity type is an n-type conductivity type and the second conductivity type is a p-type conductivity type.